Three-dimensionally-architectured GaN light emitting crystals

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**Figure S1.** (a) SEM image of broken GaN crystal. (b) SEM images of GaN crystal array embedded in PDMS and mechanically exploited from the substrate.
Figure S2. Top: TEM image (left panel) and corresponding EDS analysis result (right panel). Bottom: The corresponding elemental mapping images of Ga (green), N (purple), C (blue) and O (yellow).
Figure S3. Room temperature PL spectrum of n-type GaN crystals.